VS-ST230SPbF Series

Vishay Semiconductors

Phase Control Thyristors (Stud Version), 230 A



- Center amplifying gate
- International standard case TO-209AB (TO-93)
- · Hermetic metal case with ceramic insulator (Also available with glass-metal seal up to 1200 V)
- · Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- · Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

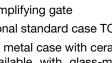
TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		230	A			
I _{T(AV)}	T _C	85	°C			
I _{T(RMS)}		360	A			
I _{TSM}	50 Hz	5700	٨			
	60 Hz	5970	A			
l ² t	50 Hz	163	– kA ² s			
1-1	60 Hz	149	KA-S			
V _{DRM} /V _{RRM}		400 to 1600	V			
t _q	Typical	100	μs			
TJ		-40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$E \begin{bmatrix} I_{DRM}/I_{RRM} & MAXIMUM & AT \\ T_{J} = T_{J} & MAXIMUM \\ & MA \end{bmatrix}$					
	04	400	500						
	08	08 800 900		30					
V3-312303	VS-ST230S 12		1300	30					
	16	1600	1700						







PRODUCT SUMMARY					
I _{T(AV)}	230 A				
V _{DRM} /V _{RRM}	400 V, 1600 V				
V _{TM}	1.55 V				
I _{GT}	150 mA				
TJ	-40 °C to 125 °C				
Package	TO-209AB (TO-93)				
Diode variation	Single SCR				



RoHS COMPLIANT

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ABSOLUTE MAXIMUM RATINGS	5						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS	
Maximum average on-state current	I	190° condu	ction. half sine v	NOVO	230	Α	
at case temperature	I _{T(AV)}		ction, nan sine v	wave	85	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 78 °C	case temperat	ure	360		
		t = 10 ms	No voltage		5700		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		5970	A kA ² s	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		4800		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	5000		
Maviation 12t for fusion		t = 10 ms N	No voltage	initial T _J = T _J maximum	163		
	l ² t	t = 8.3 ms	reapplied		148		
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{RRM}		115		
			reapplied		105	1	
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	reapplied	1630	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x _{T(AV)} < l < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.92	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	num	0.98	v		
Low level value of on-state slope resistance	r _{t1}	$(16.7 \% x \pi x I_{T(AV)} < I < \pi x I_{T(AV)}), T_J = T_J maximum$			0.88	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.81	1115.2	
Maximum on-state voltage	V _{TM}	$I_{pk} = 720 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.55	V	
Maximum holding current	Ι _Η	T _ 25 °C	anada ayanbu 1	2. V registive load	600	mA	
Maximum (typical) latching current	١ _L	$i_{\rm J} = 25^{-1}$ C,	anoue supply 1	2 V resistive load	1000 (300)	ma	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,$ $t_r \leq 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	
Typical turn-off time	tq	$\begin{split} I_{TM} &= 300 \text{ A}, T_J = T_J \text{ maximum, } dI_F/dt = 20 A/\mu\text{s}, \\ V_R &= 50 V, dV/dt = 20 V/\mu\text{s}, \text{ gate } 0 V 100 \Omega, t_p = 500 \mu\text{s} \end{split}$	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM} $T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied		30	mA



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TRIGGERING						
PARAMETER	SYMBOL	т	TEST CONDITIONS			UNITS
PARAMETER	STIVIDUL	•	TEST CONDITIONS		MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10).0	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	А
Maximum peak positive gate voltage	+ V _{GM}		t < 5 mg	20		V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum,	5.0		v	
		T _J = - 40 °C		180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		90	150	mA
		T _J = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	40	-	
		T _J = - 40 °C	value which will trigger all units 12 V anode to cathode applied	2.9	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	v anode to cathode applied	1.8	3.0	V
		T _J = 125 °C		1.2	-	
DC gate current not to trigger	I _{GD}	т. т	Maximum gate current/voltage not to trigger is the maximum value	e		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS				
Maximum operating junction temperature range	TJ		-40 to 125	°C				
Maximum storage temperature range	T _{Stg}		-40 to 150					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	K/W				
Maximum thermal resistance, case to heatsink	R _{thC-hs}	Mounting surface, smooth, flat and greased	0.04					
Mounting torque + 10.0/		Non-lubricated threads	31 (275)	N · m				
Mounting torque, ± 10 %		Lubricated threads	24.5 (210)	(lbf · in)				
Approximate weight			280	g				
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)				

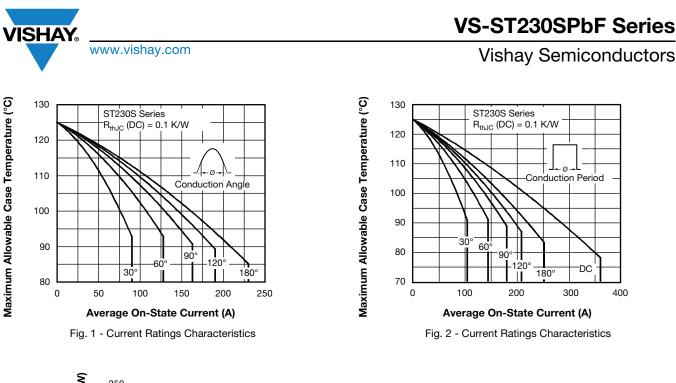
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.016	0.012					
120°	0.019	0.020					
90°	0.025	0.027	$T_J = T_J$ maximum	K/W			
60°	0.036	0.037					
30°	0.060	0.060					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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 3
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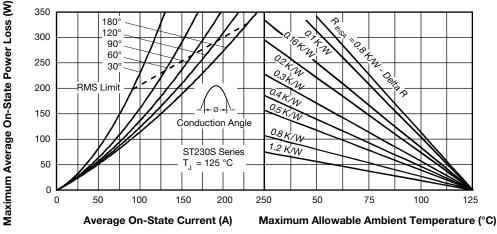
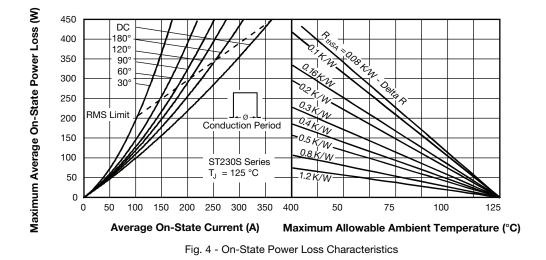


Fig. 3 - On-State Power Loss Characteristics





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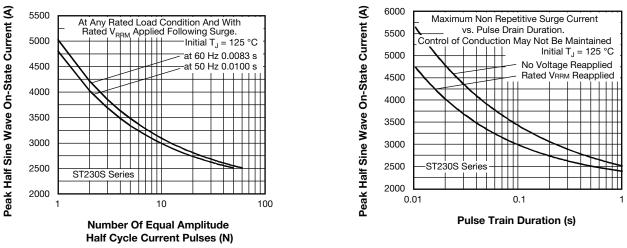


Fig. 5 - Maximum Non-Repetitive Surge Current



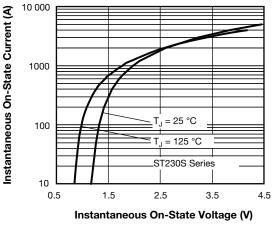


Fig. 7 - On-State Voltage Drop Characteristics

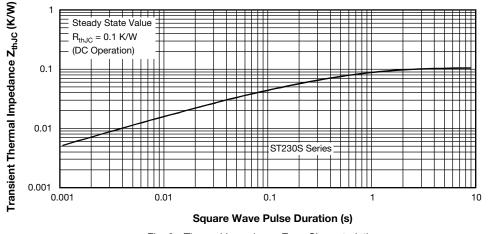
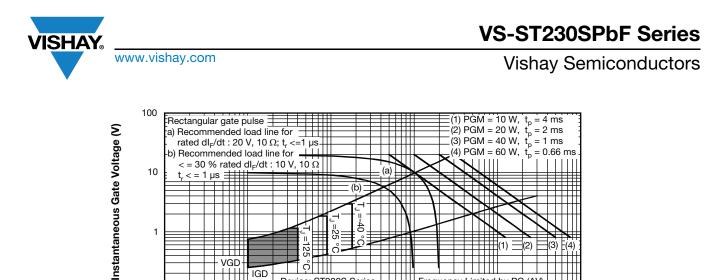


Fig. 8 - Thermal Impedance ZthJC Characteristics

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Instantaneous Gate Current (A)

Frequency Limited by PG (AV)

10

100

Device: ST230S Series

0.1

0.01

Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

0.1

Device code	VS-	ST	23	0	S	16	Ρ	0	v	PbF
	1	2	3	4	5	6	7	8	9	10
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	 Thy Ess 0 = S = Volt 	ristor ential pa Conver Compre	niconduo art numl ter grado ession b de x 100 ase 3/4"-	oer e onding = V _{RRN}	stud ₁ (see V	-	Ratings	table)	
	7 - 8 -	0 =	Eyelet t	erminals termina	s (gate a	and aux	iliary ca		-	
	9 -			s-metal s ceramic)		
	10 - -			ndard p d (Pb)-fr		n				

Note: For metric device M16 x 1.5 contact factory

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95082					

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 6
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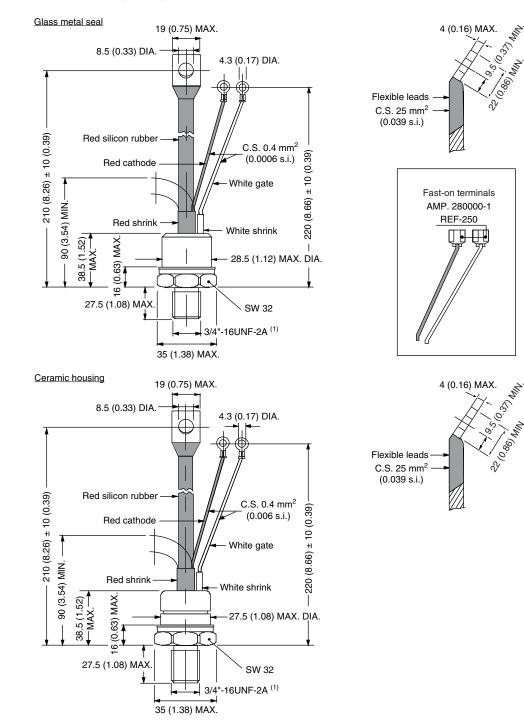
J.

NIN,



DIMENSIONS in millimeters (inches)

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Note

⁽¹⁾ For metric device: M16 x 1.5 - length 21 (0.83) maximum

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